

1. Physics of Semiconductor Devices

Oct. 2, 2018

Physics of Semiconductor Devices

- Diodes, solid state lasers, transistors
- Computing, communications
- Controllers: vacuum cleaners, coffee makers, etc.
- Transportation, autonomous driving, electric cars
- Efficient lighting, solar cells, displays
- Lasers

Peter Hadley

Home
Outline
Introduction
Crystals
Intrinsic Semiconductors
Extrinsic Semiconductors
Transport
pn junctions
Contacts
JFETs/MESFETs
MOSFETs
Bipolar transistors
Opto-electronics
Lectures
Exam questions
Making presentations
TUG students
Student projects

http://www.if.tugraz.at/psd.html

The screenshot shows a Mozilla Firefox browser window. The address bar contains the URL `http://lamp.tu-graz.ac.at/~hadley/psd/L0/index.php`. The page title is "Physics of Semiconductor Devices". The navigation menu on the left lists: Home, Introduction, Crystals, Band structure, Doping, Transport, pn junctions I, pn junctions II, Contacts, JFETs/MESFETs, MOSFETs I, MOSFETs II, MOSFETs III, Bipolar I, Bipolar II, Opto-electronics, Lectures, Problems, Login, and TUG students. The main content area contains two paragraphs of text.

Student: **Not logged in**

Physics of Semiconductor Devices

Semiconductor devices are widely used in computation and control systems. Computers, telephones, medical instruments, automobiles, and household appliances make heavy use of semiconductors. This course explains the how semiconductor devices work. Before the devices themselves are discussed, a few concepts of solid state physics will be presented. Solid state physics is the study of how atoms arrange themselves into solids and what properties these solids have. Properties that can be calculated using the principles of solid state physics include electrical conductivity, thermal conductivity, elasticity, yield strength, speed of sound, dielectric constant, magnetism, and piezoelectricity.

A proper understanding of the electronic properties of materials is only possible when the electrons are described quantum mechanically. Therefore, a brief discussion of quantum mechanics will be necessary. After a few principles of quantum mechanics are introduced, the electronic properties of metals, insulators, and semiconductors will be described. Electronic devices typically consist of different materials and the behavior of the electrons at the interfaces between the materials is very important. The properties of electronic materials and the interfaces between electronic materials can be used to explain the behavior of a variety of semiconductor devices such as light emitting diodes, solid state lasers, sensors, bipolar transistors, and field effect transistors. A device that is used extensively in integrated circuits is the MOSFET (Metal Oxide Semiconductor Field Effect Transistor). We will spend several weeks discussing the properties of MOSFETs.

Physik der Halbleiterbauelemente

513.221 16W

Here you can browse all available course videos. Use the search box to look for a specific term. Click an item from the list on the left to see the related videos. Click again to select. For older videos, choose Year and Semester in the filter below.

2016

WS

Einführung in die Programmierung
706.012 16W

Einführung in die strukturierte Programmierung
NB.03001UF 16W

Grundlagen der Informatik (CS)
NB.01234UF 16W

Kurs zur Ergänzungsprüfung Darstellende Geometrie
507.056 16W

Medical Informatics
709.049 16W

Search

#14
Hadley P

laser diodes

Physik der Halbleiterbauelemente
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#13
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Change pn junction in the depletion approximation

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Exams

February 3
March 3
April 28
June 30

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MOSFETs

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Before the lecture, the slides will be uploaded to:
<https://cloud.tugraz.at/index.php/s/NjuEDwhj1R5CBGT>

Examination

1 hour written exam

One page of handwritten notes

1 Contribution to improve the course

Chapter summaries

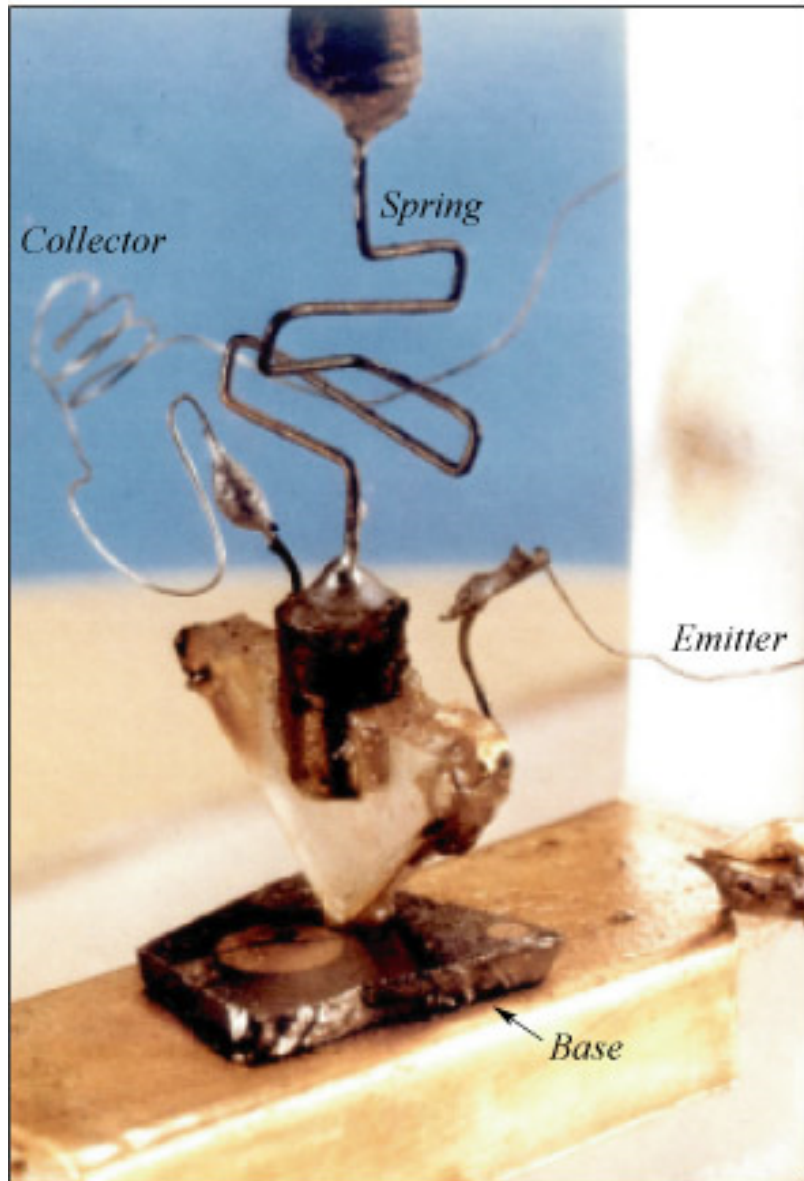
Solutions to exam questions

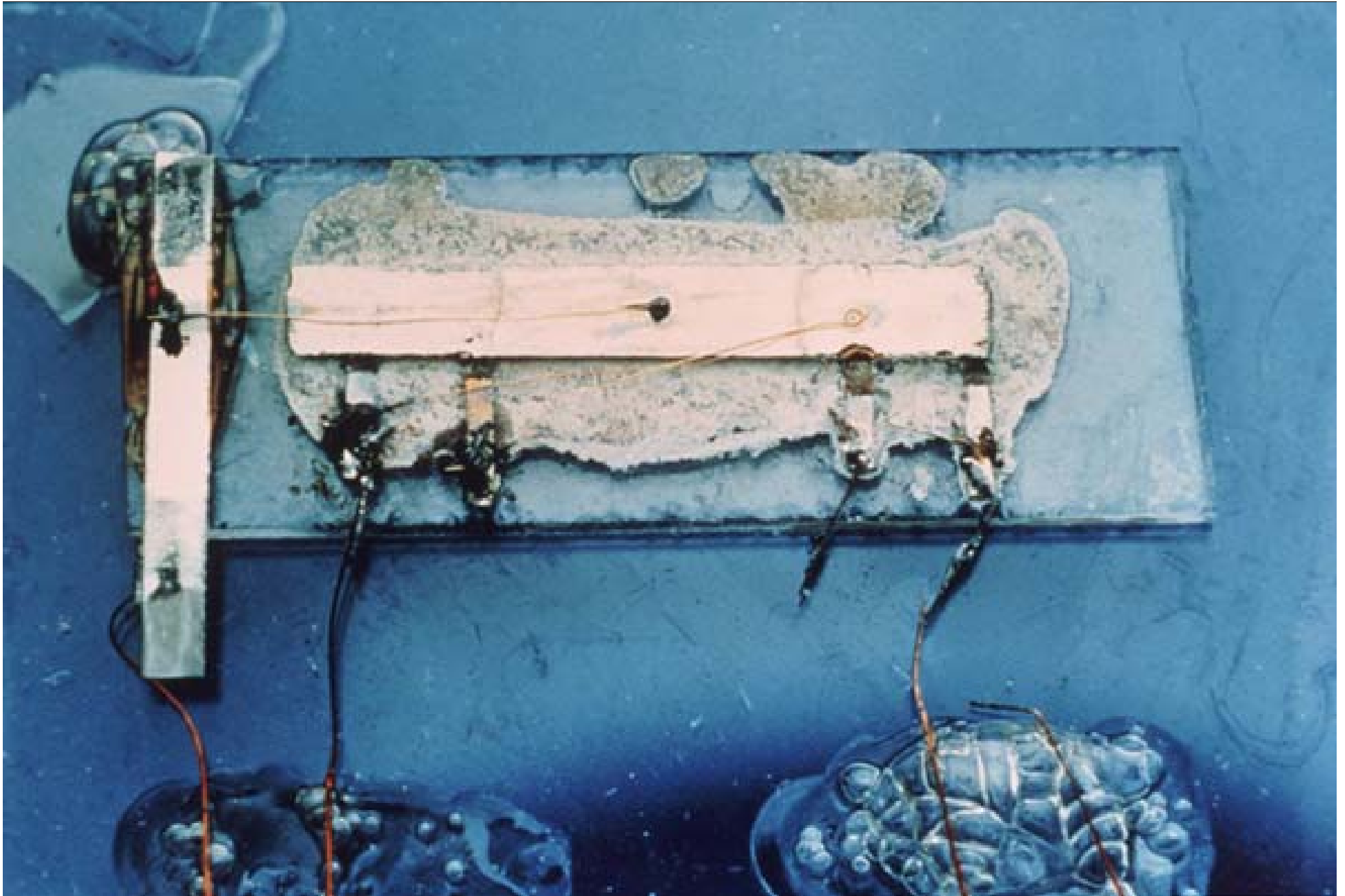
Simulations

Videos

Oral exam

The first point contact transistor
William Shockley, John Bardeen, and Walter Brattain
Bell Laboratories, Murray Hill, New Jersey (1947)





Jack Kilby's first integrated circuit 1958

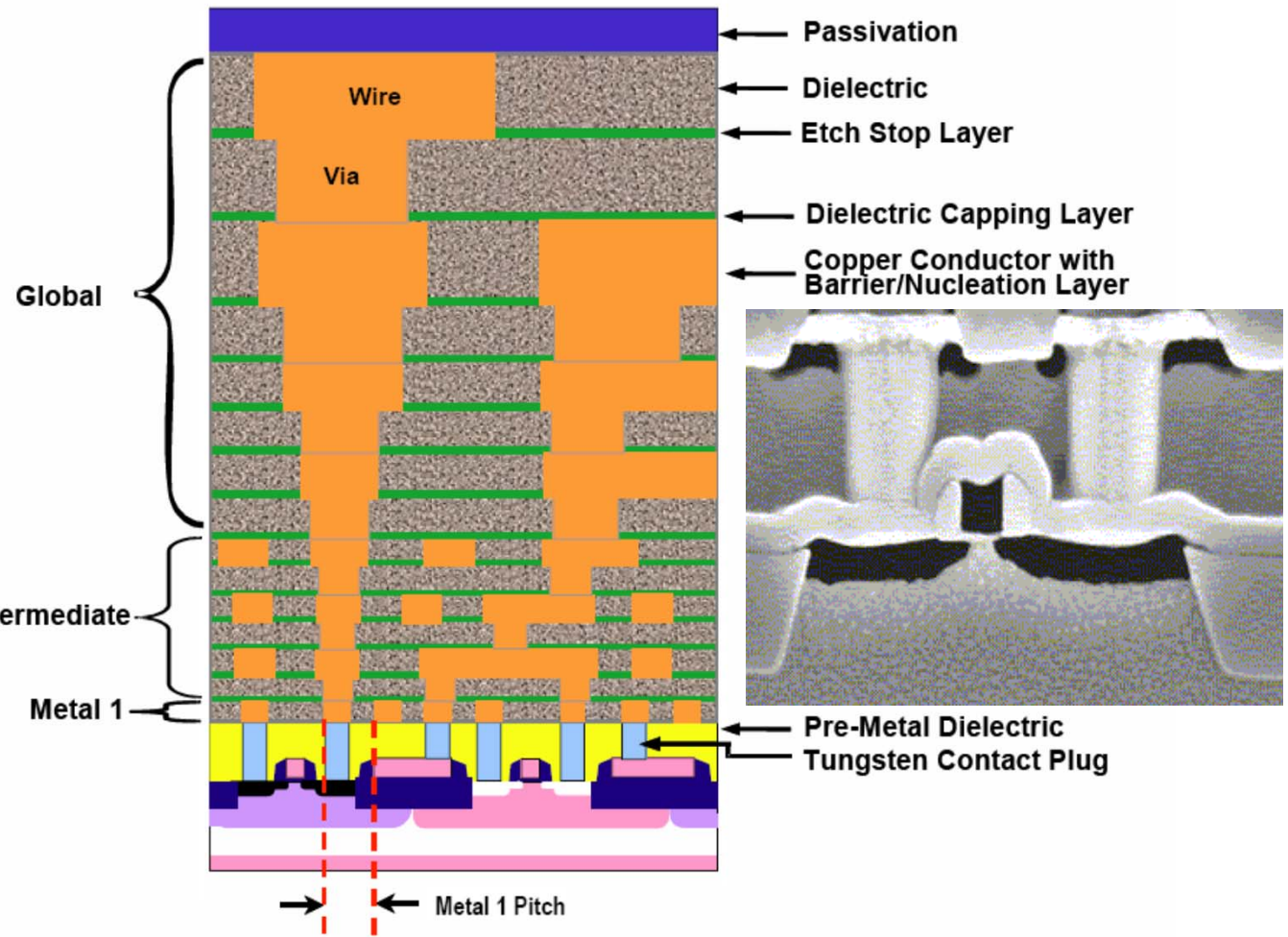
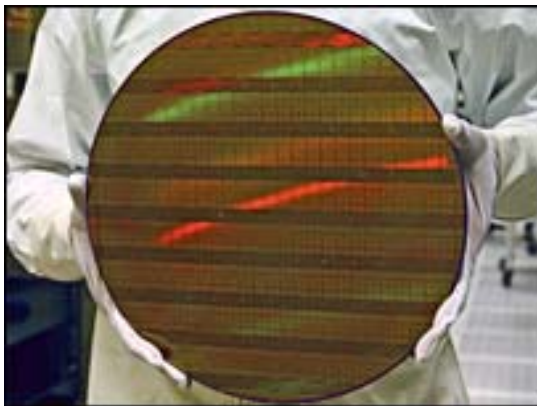
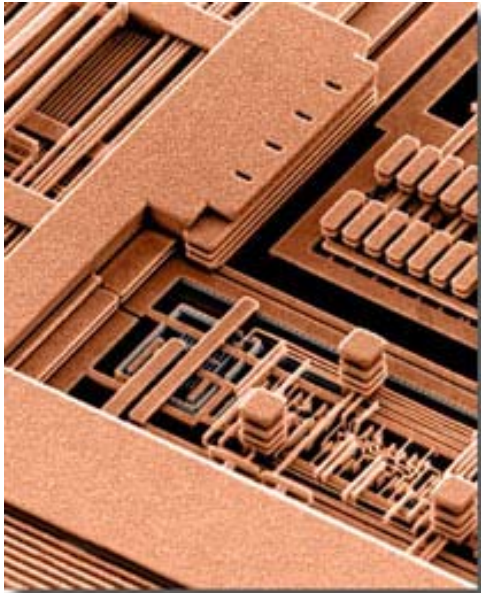
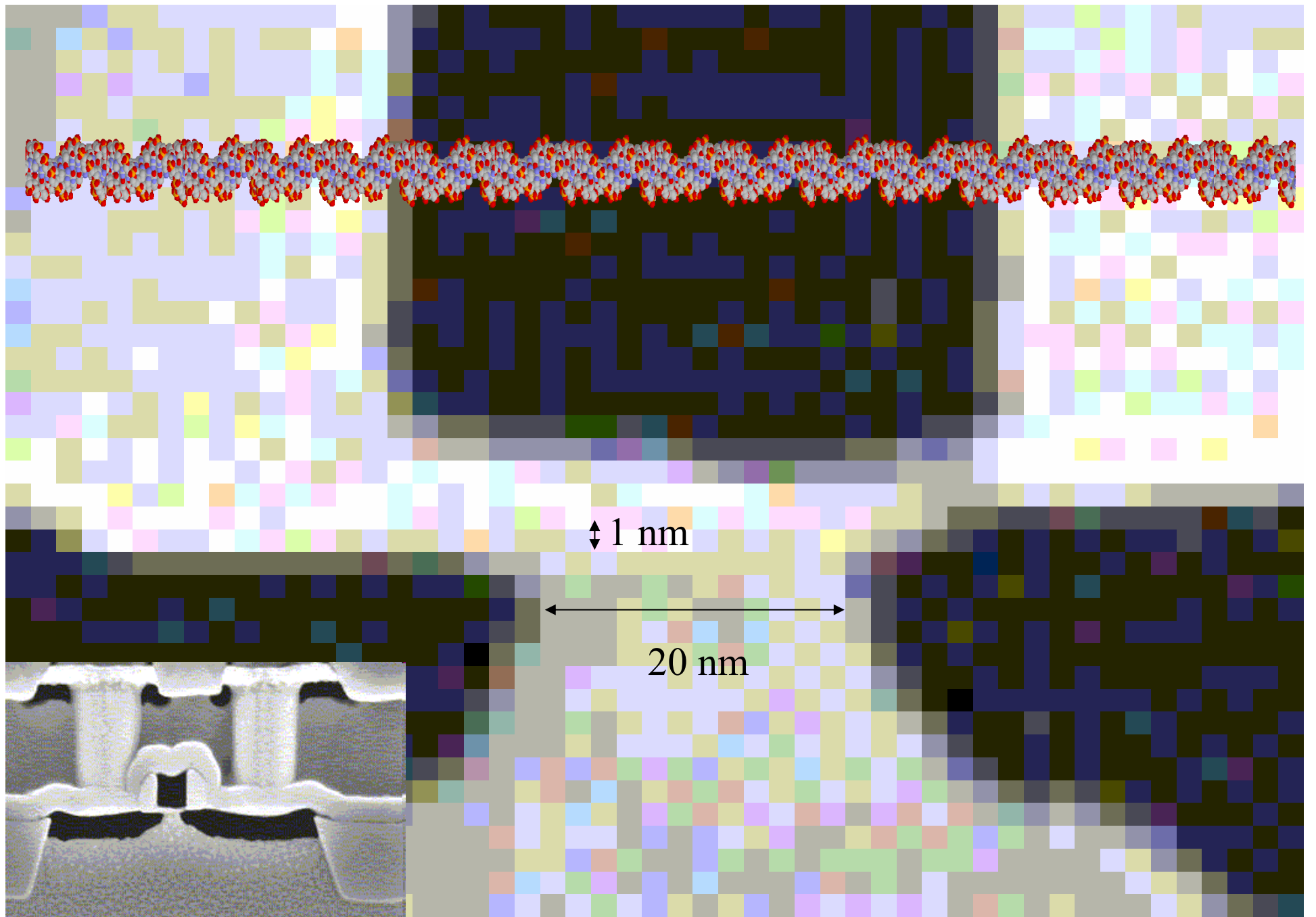


Table PIDS2a High-performance (HP) Logic Technology Requirements

node
metal 1/2 pitch
gate length

	2013	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028
node	"16/14"		"11/10"		"8/7"		"6/5"		"4/3"		"3/2.5"		"2/1.5"		"1/0.75"	
metal 1/2 pitch	40	32	32	28.3	25.3	22.5	20.0	17.9	15.9	14.2	12.6	11.3	10.0	8.9	8	7.1
gate length	20	18	16.7	15.2	13.9	12.7	11.6	10.6	9.7	8.8	8.0	7.3	6.7	6.1	5.6	5.1





<https://irds.ieee.org>

INTERNATIONAL ROADMAP FOR DEVICES AND SYSTEMS™



INTERNATIONAL ROADMAP FOR DEVICES AND SYSTEMS

INTERNATIONAL
ROADMAP
FOR
DEVICES AND SYSTEMS

2017 EDITION

EXECUTIVE SUMMARY

1. Application Benchmarking (AB)
2. Systems and Architectures (SA)
3. Outside System Connectivity (OSC)
4. More Moore (MM) ←
5. Beyond CMOS (BC) ←
6. Packaging Integration (PI)
7. Factory Integration (FI)
8. Lithography (L)
9. Emerging Research Materials (ERM) ←
10. Yield Enhancement (YE)
11. Metrology (M)
12. Environment, Safety, Health (ESH/S), and Sustainability

YEAR OF PRODUCTION	2017	2019	2021	2024	2027	2030	2033
	P54M36	P48M28	P42M24	P36M21	P32M14	P32M14T2	P32M14T4
Logic industry "Node Range" Labeling (nm)	"10"	"7"	"5"	"3"	"2.1"	"1.5"	"1.0"
IDM-Foundry node labeling	i10-f7	i7-f5	i5-f3	i3-f2.1	i2.1-f1.5	i1.5-f1.0	i1.0-f0.7
Logic device structure options	finFET FDSOI	finFET LGAA	LGAA finFET	LGAA VGAA	LGAA VGAA	VGAA, LGAA 3DVLSI	VGAA, LGAA 3DVLSI
Logic device mainstream device	finFET	finFET	LGAA	LGAA	LGAA	VGAA	VGAA
DEVICE STRUCTURES							
LOGIC DEVICE GROUND RULES							
MPU/SoC Metalx 1/2 Pitch (nm)[1,2]	18.0	14.0	12.0	10.5	7.0	7.0	7.0
MPU/SoC Metal0/1 1/2 Pitch (nm)	18.0	14.0	12.0	10.5	7.0	7.0	7.0
Contacted poly half pitch (nm)	27.0	24.0	21.0	18.0	16.0	16.0	16.0
L _g : Physical Gate Length for HP Logic (nm) [3]	20	18	16	14	12	12	12
L _g : Physical Gate Length for LP Logic (nm)	22	20	18	16	14	14	14
Channel overlap ratio - two-sided	0.80	0.80	0.80	0.80	0.80	0.80	0.80
Spacer width (nm)	8	7	6	5	5	5	5
Contact CD (nm) - finFET, LGAA	18	16	14	12	10		
Contact CD (nm) - VGAA						12	12
Device architecture key ground rules							
FinFET Fin Half-pitch (nm)	16.0	14.0					
FinFET Fin Width (nm)	8.0	7.0					
FinFET Fin Height (nm)	45	50					
Footprint drive efficiency - finFET	3.06	3.82					
Lateral GAA lateral half-pitch (nm)			12.0	10.5	9.0		
Lateral GAA vertical half-pitch (nm)			8.0	8.0	8.0		
Lateral GAA (nanosheet) thickness (nm)			5.0	5.0	5.0		
Lateral GAA (nanosheet) minimum width (nm)			7.0	7.0	6.0		
Number of vertically stacked nanosheets			3	4	5		
Device height (nm)			47	63	79		
Footprint drive efficiency - lateral GAA			3.00	4.57	6.11		
Vertical GAA lateral half-pitch (nm)						7.0	7.0
Vertical GAA width (nm)						6.0	6.0
Contact-gate enclosure (nm)						2.0	2.0
Footprint drive efficiency - vertical GAA						1.7	1.7
Device effective width (nm)	98.0	107.0	72.0	96.0	110.0	24.0	24.0
Device lateral half pitch (nm)	16.0	14.0	12.0	10.5	9.0	7.0	7.0
Device height (nm)	45.0	50.0	47.0	63.0	79.0	24.0	24.0
Minimum device width (fin, nanosheet) or diameter (nm)	8.0	7.0	7.0	7.0	6.0	6.0	6.0

Conductivity

Al: $\sigma = 3.5 \times 10^7 \text{ 1}/\Omega \cdot \text{m}$

Si: $\sigma = 4.3 \times 10^{-4} \text{ 1}/\Omega \cdot \text{m}$

B Boron 10.811	C Carbon 12.011	N Nitrogen 14.007
13 Al Aluminum 26.982	14 Si Silicon 28.086	15 P Phosphorus 30.974
31 Ga Gallium 69.723	32 Ge Germanium 72.61	33 As Arsenic 74.922

Periodic Table of the Elements

1 IA 11A H Hydrogen 1.008	2 IIA 2A He Helium 4.003	3 Li Lithium 6.941	4 Be Beryllium 9.012	5 B Boron 10.811	6 C Carbon 12.011	7 N Nitrogen 14.007	8 O Oxygen 15.999	9 F Fluorine 18.998	10 Ne Neon 20.180	11 Na Sodium 22.990	12 Mg Magnesium 24.305	13 Al Aluminum 26.982	14 Si Silicon 28.086	15 P Phosphorus 30.974	16 S Sulfur 32.065	17 Cl Chlorine 35.453	18 Ar Argon 39.948	19 K Potassium 39.098	20 Ca Calcium 40.078	21 Sc Scandium 44.956	22 Ti Titanium 47.88	23 V Vanadium 50.942	24 Cr Chromium 51.996	25 Mn Manganese 54.938	26 Fe Iron 55.933	27 Co Cobalt 58.933	28 Ni Nickel 58.693	29 Cu Copper 63.546	30 Zn Zinc 65.39	31 Ga Gallium 69.732	32 Ge Germanium 72.61	33 As Arsenic 74.922	34 Se Selenium 78.09	35 Br Bromine 79.904	36 Kr Krypton 84.80	37 Rb Rubidium 84.464	38 Sr Strontium 87.62	39 Y Yttrium 88.905	40 Zr Zirconium 91.224	41 Nb Niobium 92.905	42 Mo Molybdenum 95.94	43 Tc Technetium 98.907	44 Ru Ruthenium 101.07	45 Rh Rhodium 102.906	46 Pd Palladium 106.42	47 Ag Silver 107.868	48 Cd Cadmium 112.411	49 In Indium 114.818	50 Sn Tin 118.71	51 Sb Antimony 121.760	52 Te Tellurium 127.6	53 I Iodine 126.904	54 Xe Xenon 131.29	55 Cs Cesium 132.905	56 Ba Barium 137.327	57-71 Lanthanide Series	72 Hf Hafnium 178.49	73 Ta Tantalum 180.948	74 W Tungsten 183.85	75 Re Rhenium 186.207	76 Os Osmium 190.23	77 Ir Iridium 192.22	78 Pt Platinum 195.08	79 Au Gold 196.967	80 Hg Mercury 200.59	81 Tl Thallium 204.383	82 Pb Lead 207.2	83 Bi Bismuth 208.980	84 Po Polonium [209]	85 At Astatine [210]	86 Rn Radon [222]	87 Fr Francium [223]	88 Ra Radium [226]	89-103 Actinide Series	104 Rf Rutherfordium [261]	105 Db Dubnium [262]	106 Sg Seaborgium [266]	107 Bh Bohrium [264]	108 Hs Hassium [265]	109 Mt Meitnerium [268]	110 Ds Darmstadtium [271]	111 Rg Roentgenium [272]	112 Cn Copernicium [285]	113 Uut Ununtrium [288]	114 Fl Flerovium [289]	115 Uup Ununpentium [293]	116 Lv Livermorium [293]	117 Uus Ununseptium [294]	118 Uuo Ununoctium [294]
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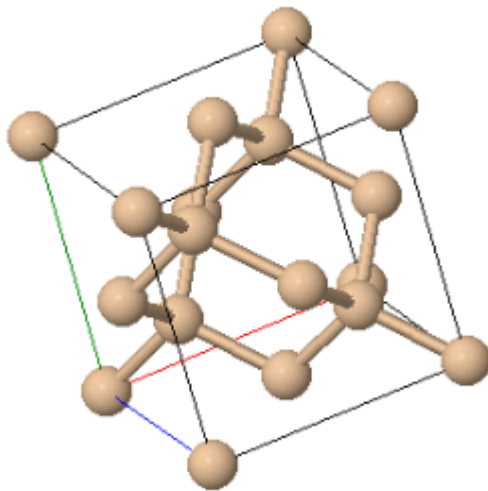
57 La Lanthanum 138.905	58 Ce Cerium 140.115	59 Pr Praseodymium 140.908	60 Nd Neodymium 144.24	61 Pm Promethium [144.913]	62 Sm Samarium 150.36	63 Eu Europium 151.965	64 Gd Gadolinium 157.25	65 Tb Terbium 158.925	66 Dy Dysprosium 162.50	67 Ho Holmium 164.930	68 Er Erbium 167.25	69 Tm Thulium 168.934	70 Yb Ytterbium 173.04	71 Lu Lutetium 174.967
89 Ac Actinium 227.028	90 Th Thorium 232.038	91 Pa Protactinium 231.036	92 U Uranium 238.029	93 Np Neptunium 237.048	94 Pu Plutonium 244.064	95 Am Americium 243.061	96 Cm Curium 247.070	97 Bk Berkelium 247.070	98 Cf Californium 251.080	99 Es Einsteinium [254]	100 Fm Fermium 257.095	101 Md Mendelevium 258.1	102 No Nobelium 259.101	103 Lr Lawrencium [262]

- Alkali Metal
- Alkaline Earth
- Transition Metal
- Semimetal
- Nonmetal
- Basic Metal
- Halogen
- Noble Gas
- Lanthanide
- Actinide

Silicon

- Important semiconducting material
- 2nd most common element on earth's crust (rocks, sand, glass, concrete)
- Often doped with other elements
- Oxide SiO_2 is a good insulator

2.33		28.086
	Si	14
5.43	$3s^2 3p^2$	
1683	DIA	625

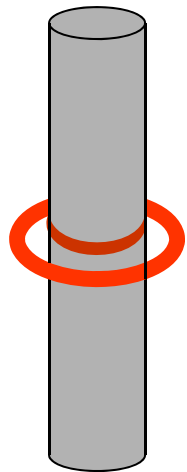
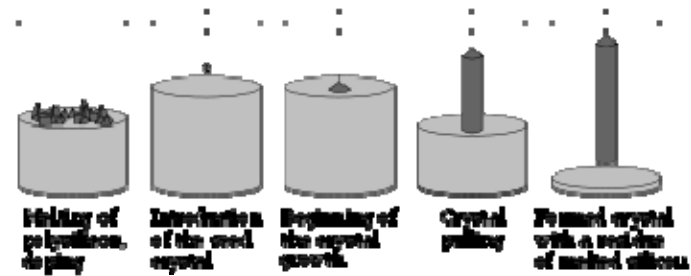


silicon crystal = diamond crystal structure

Silicon

Large (2 m) single crystals are grown

Czochralski process

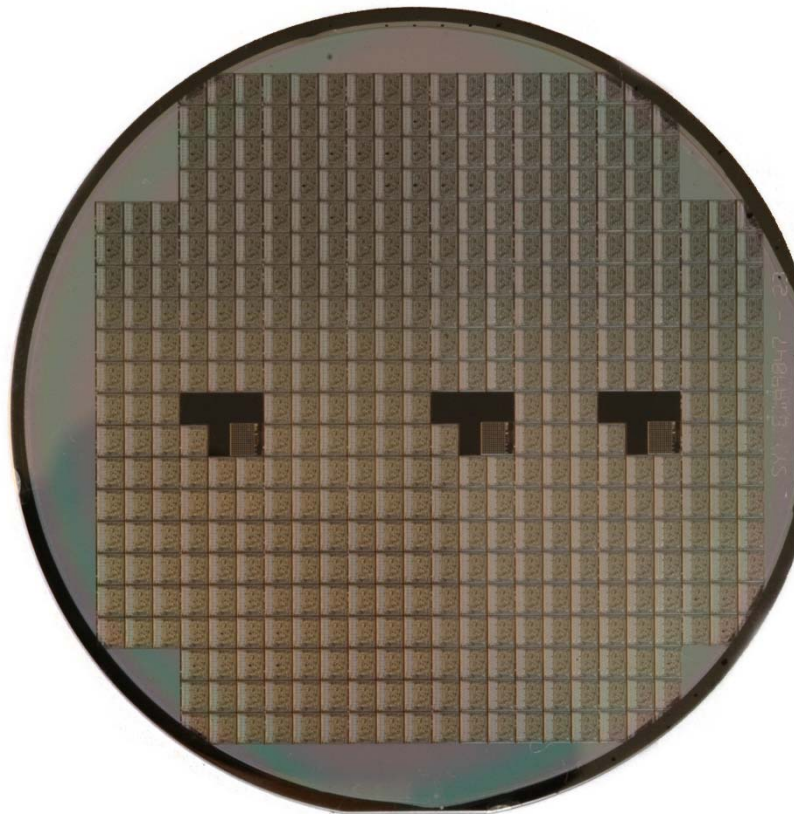


Float zone

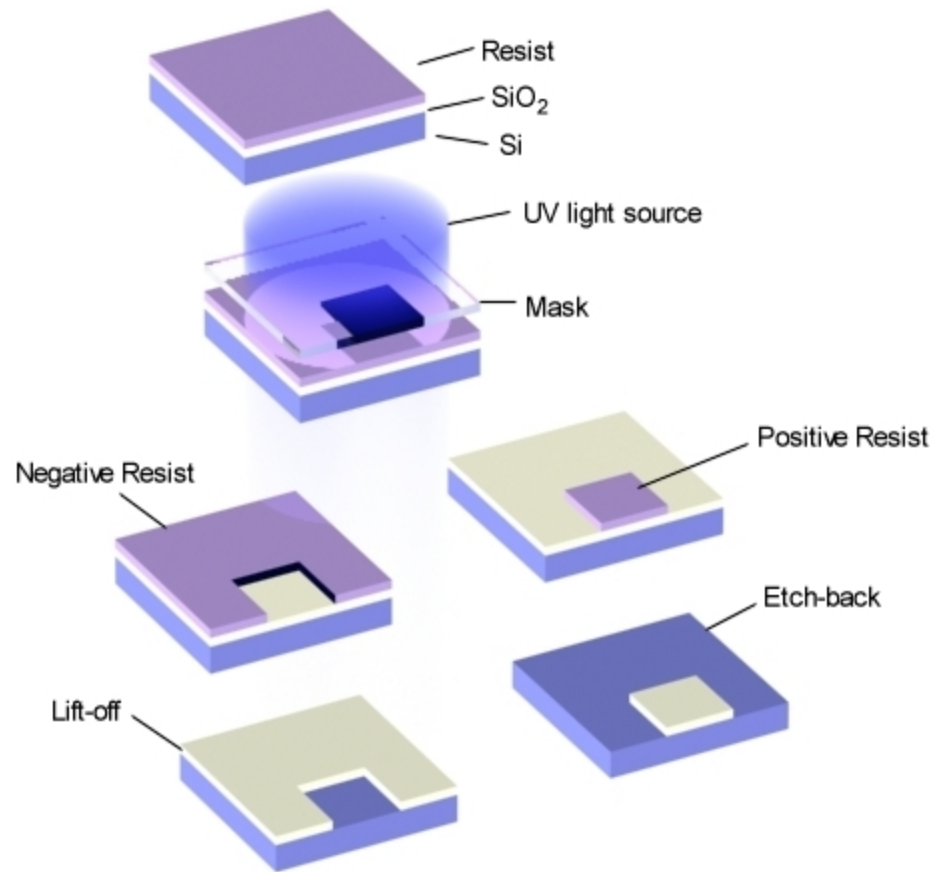


Silicon wafers

50 μm - 0.5 mm thick



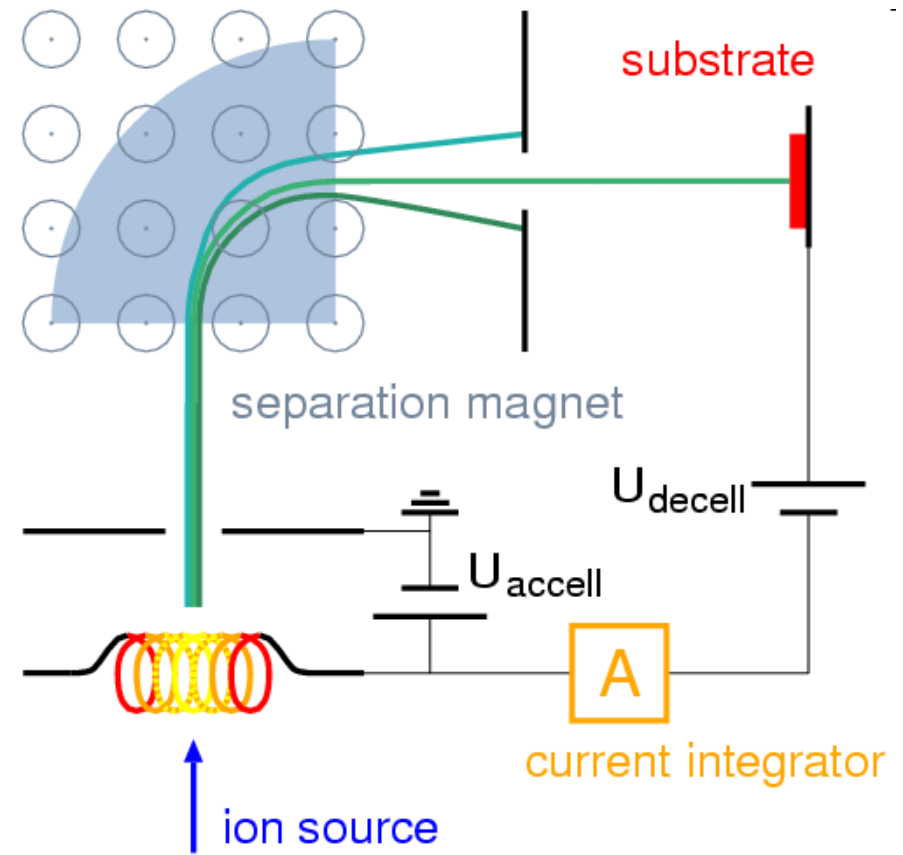
Photolithography



<http://britneyspears.ac/physics/fabrication/photolithography.htm>

<http://cleanroom.byu.edu/lithography.parts/Lithography.html>

Ion implantation



Implant at 7° to avoid channeling

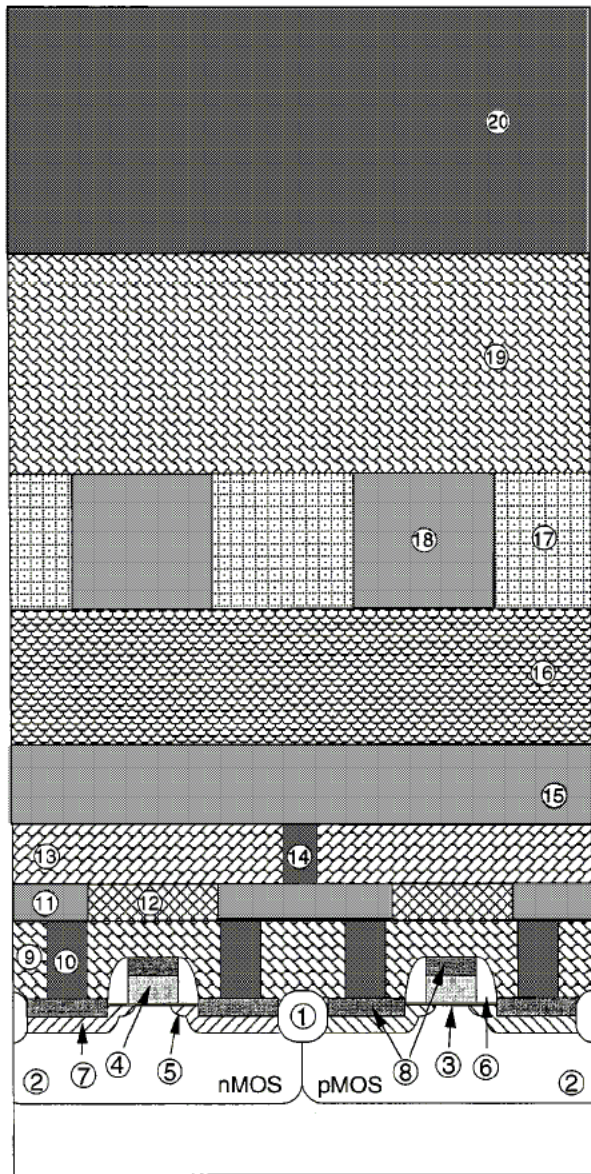
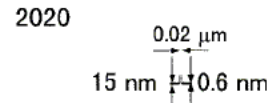
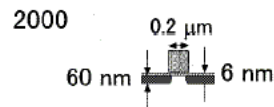
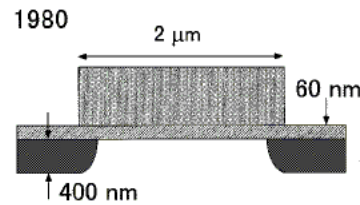
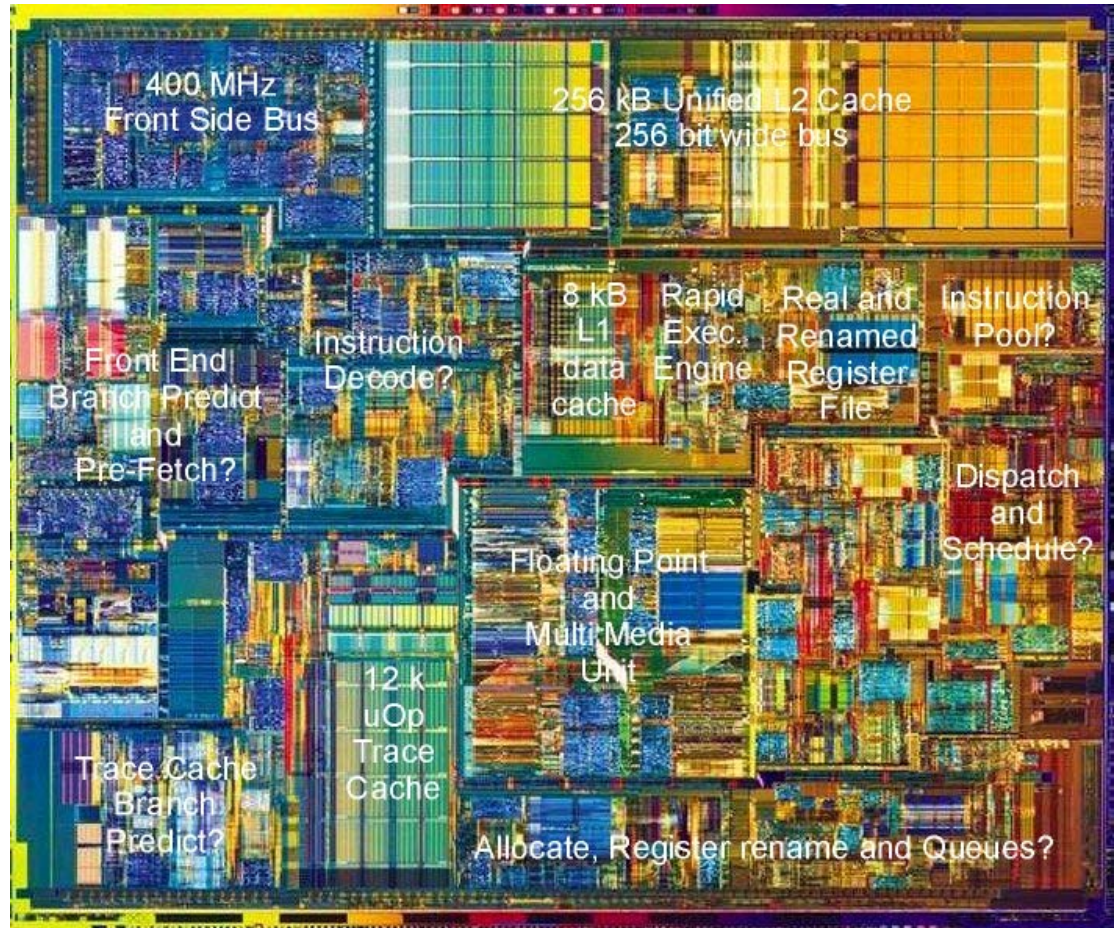
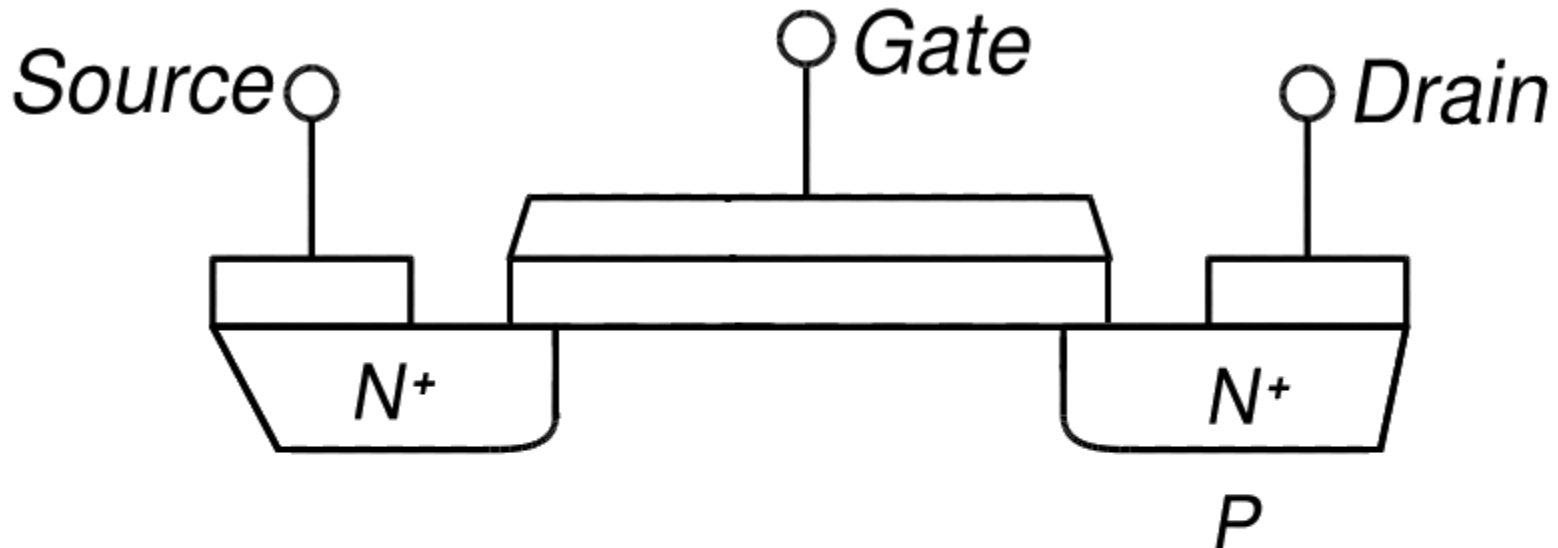


Fig. 2 Schematic cross section of present CMOS FETs with multilayered wiring.



MOSFET

Metal Oxide Semiconductor Field Effect Transistor



functions as a switch
~ 1 billion /chip

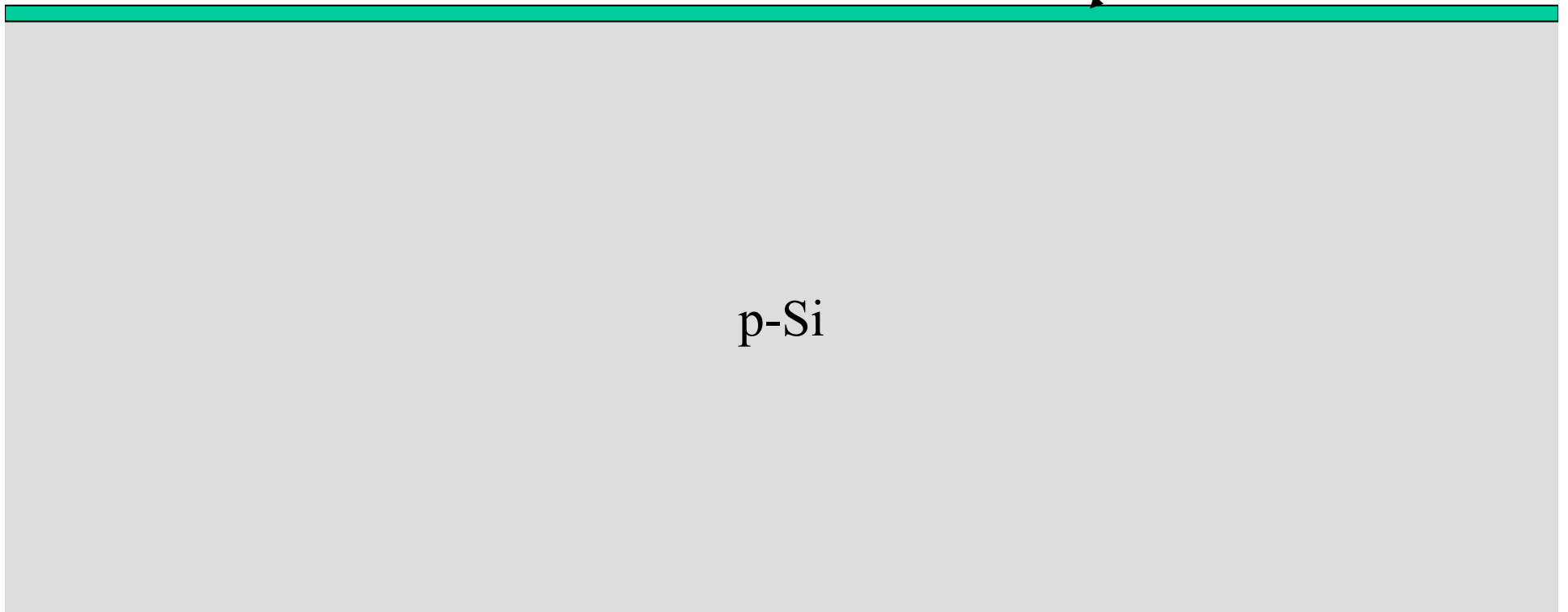
Self-aligned fabrication

p-Si 100 wafer

Dry oxidation

SiO₂ gate oxide

p-Si



photoresist

polysilicon

CVD: SiH_4 @ 580 to 650 °C

SiO_2

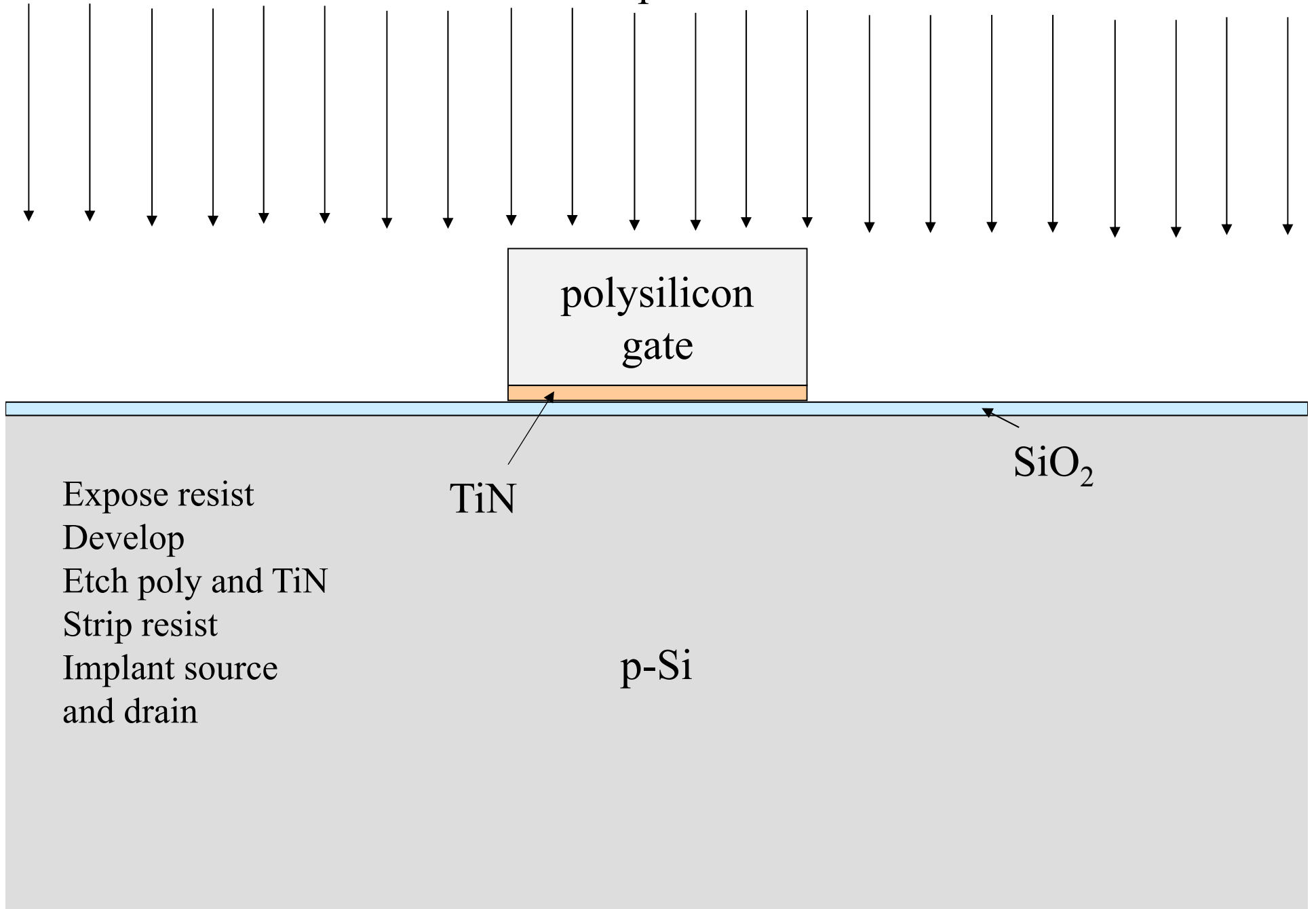
TiN (CVD)

30–70 $\mu\Omega\cdot\text{cm}$ Conductive diffusion barrier

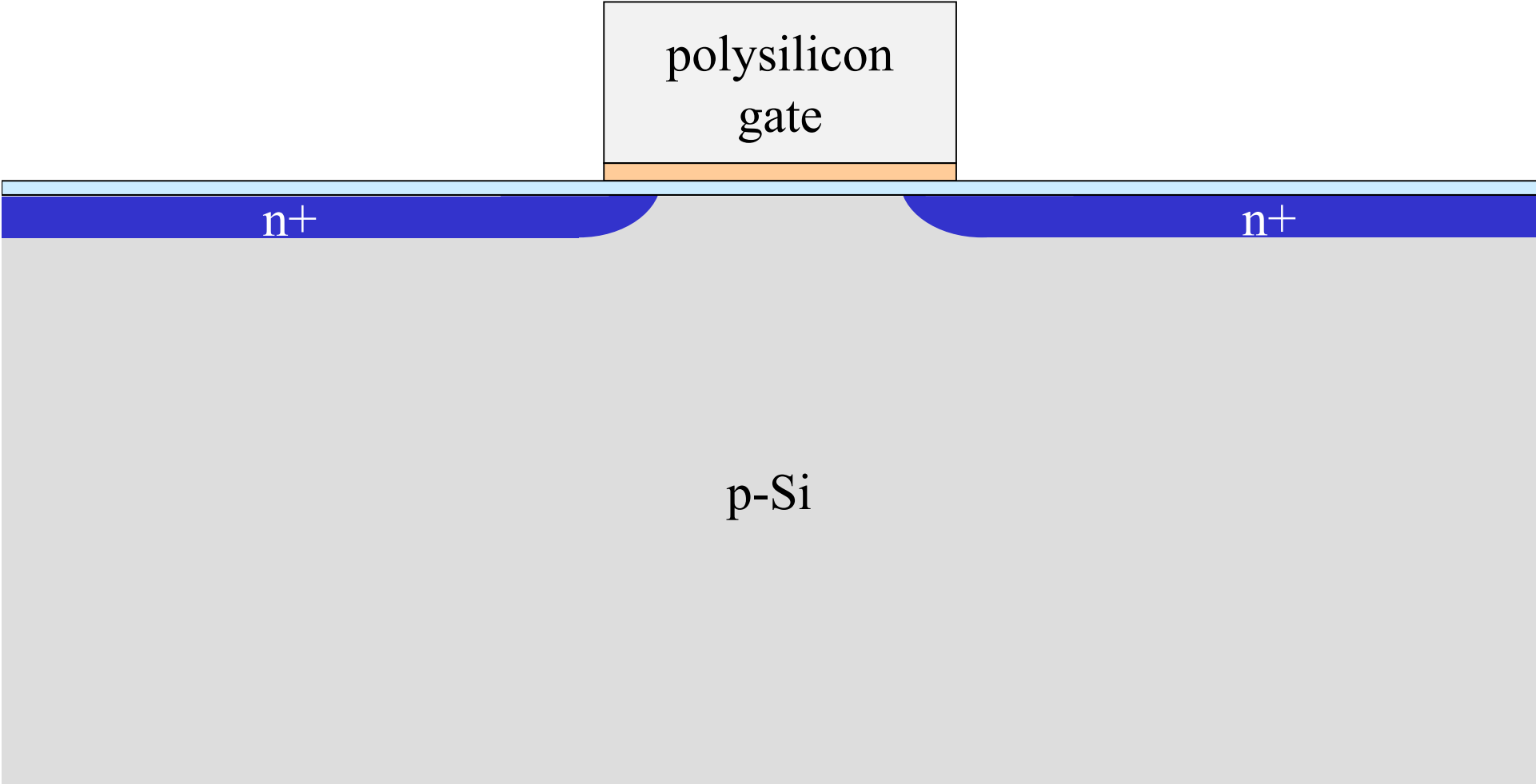
p-Si



Implant



Self-aligned fabrication



Spacer

PECVD SiN_x

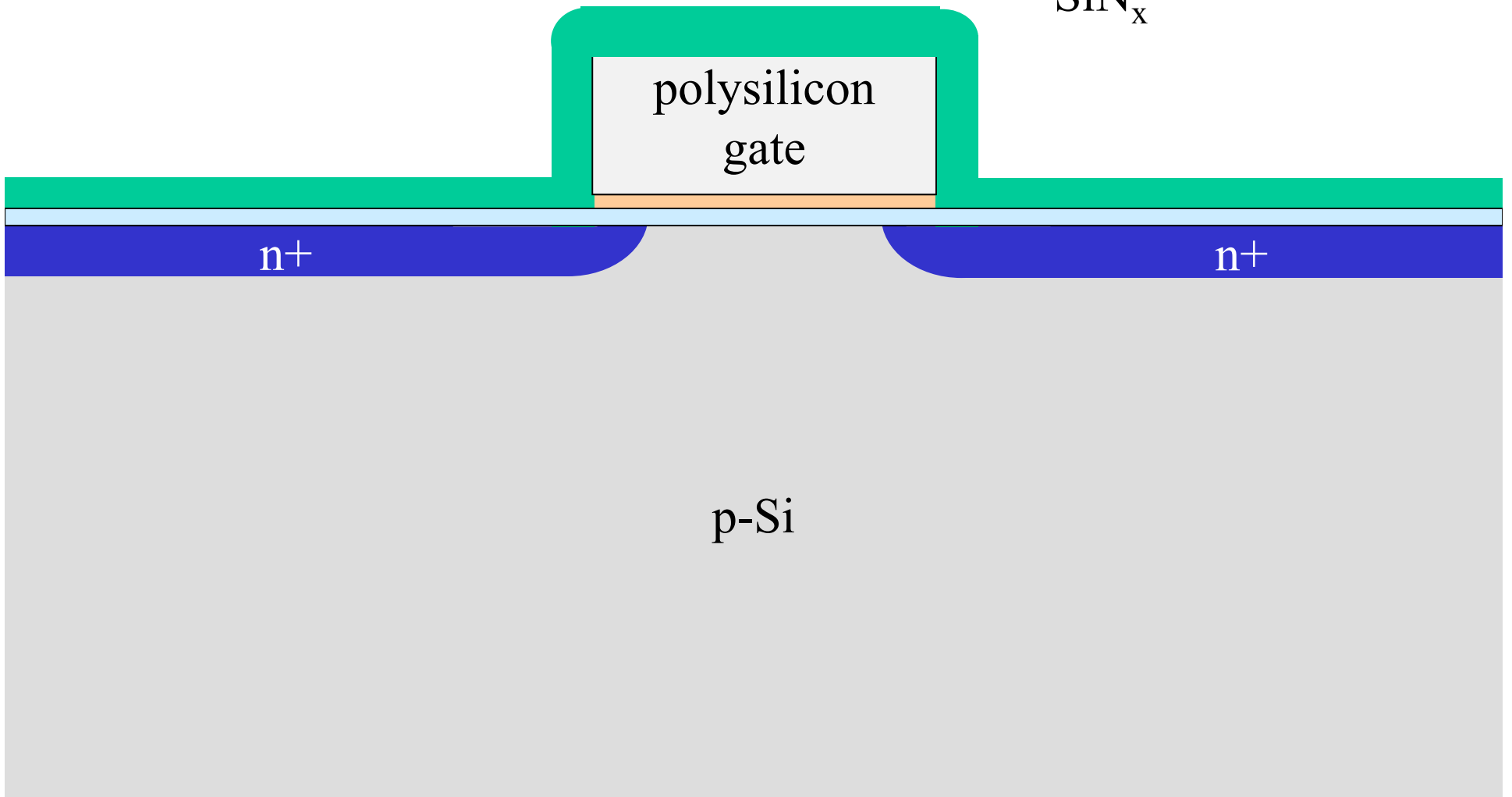
SiN_x

polysilicon
gate

n+

n+

p-Si



Spacer

Etch back to
leave only
sidewalls

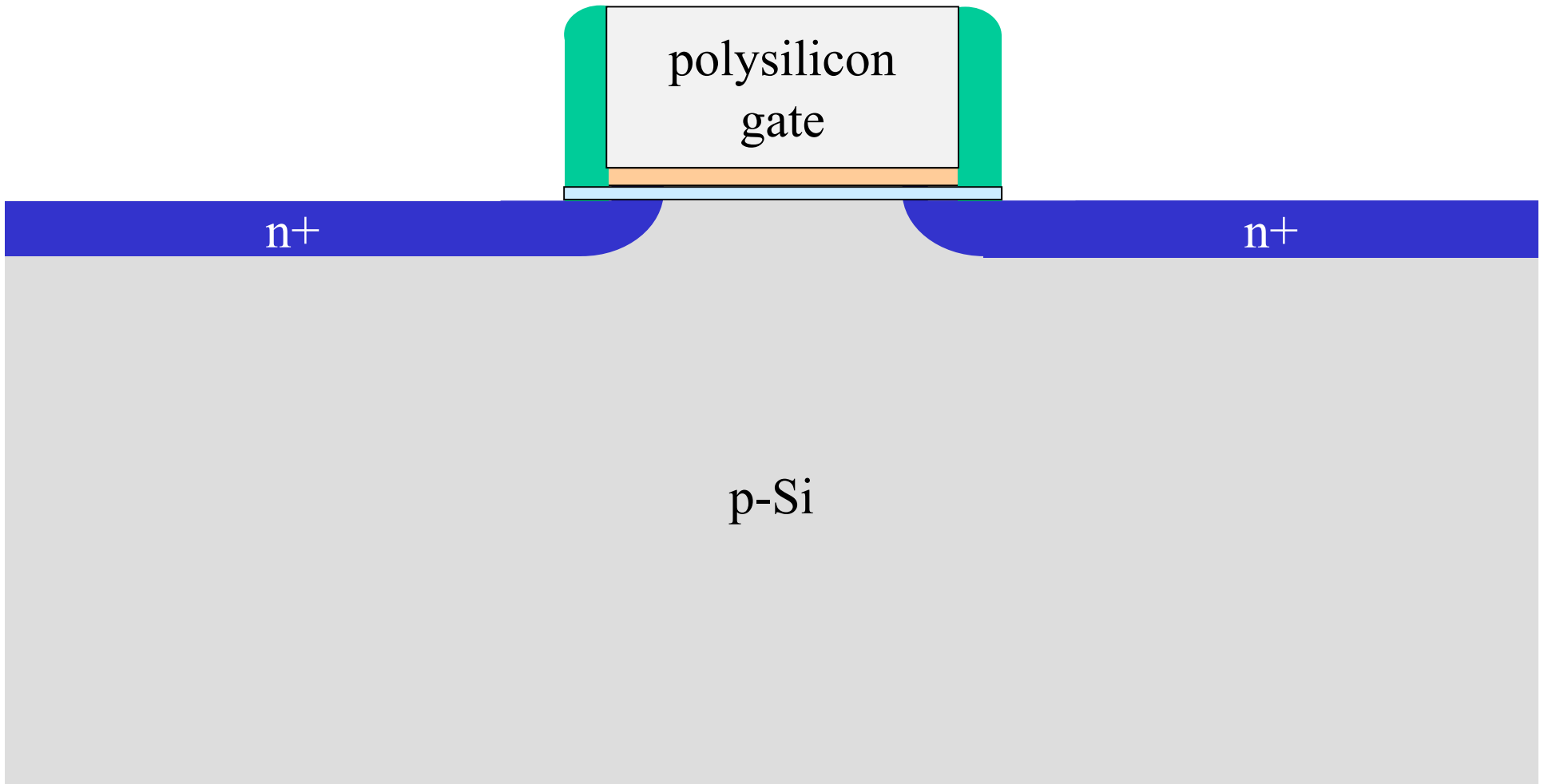
SiN_x

polysilicon
gate

n+

n+

p-Si



Implant

